

UTC UNISONIC TECHNOLOGIES CO., LTD

40N15 **Power MOSFET**

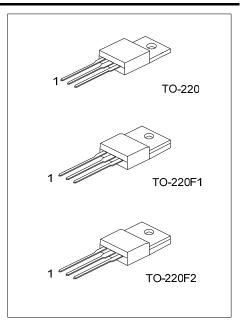
40A, 150V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC 40N15 is a N-channel enhancement MOSFET, it uses UTC's advanced technology to provide the customers with perfect R_{DS(ON)}, high switching speed, high current capacity and low gate charge.

FEATURES

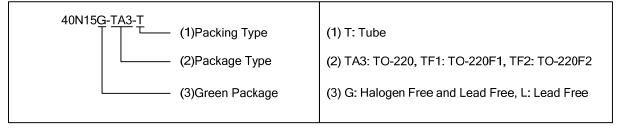
- * $R_{DS(ON)}$ < 50m Ω @ V_{GS} =10V, I_D =20A
- * High Switching Speed
- * High Current Capacity



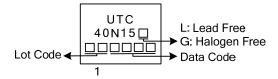
ORDERING INFORMATION

Pir	Ordering Number	Pin Assignment			
ge 1	Lead Free Halogen Free Package	2	3	Packing	
0 G	40N15L-TA3-T 40N15G-TA3-T TO-220	D	S	Tube	
F1 G	40N15L-TF1-T 40N15G-TF1-T TO-220F1	D	S	Tube	
F2 G	40N15L-TF2-T 40N15G-TF2-T TO-220F2	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	150	V
Gate-Source Voltage		V_{GSS}	±25	V
Drain Current	Continuous	I _D	40	Α
	Pulsed	I _{DM}	180	Α
Avalanche Current		I _{AR}	45.6	Α
Avalanche Energy	Single Pulsed	E _{AS}	650	mJ
	Repetitive	E _{AR}	21	mJ
Peak Diode Recovery dv/dt		dv/dt	7	V/ns
Power Dissipation	TO-220	Ь	166	W
	TO-220F1/TO-220F2	P _D	40	W
Junction Temperature		T_J	-50 ~ + 150	°C
Storage Temperature Range		T _{STG}	-50 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

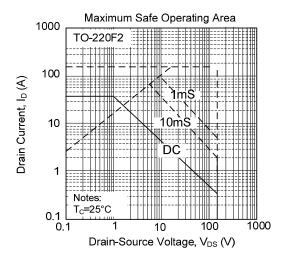
■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient		θ_{JA}	62.5	°C/W	
Junction to Case	TO-220	θ _{JC}	0.9	°C/W	
	TO-220F1/TO-220F2		3.125	°C/W	

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	YMBOL TEST CONDITIONS		TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	150			V	
Drain-Source Leakage Current	I _{DSS}	V _{GS} =0V, V _{DS} =150V			900	nA	
Forward		V _{GS} =+20V, V _{DS} =0V			+100	nA	
Gate-Source Leakage Current Reverse	I_{GSS}	V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.2		3.8	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A			50	mΩ	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	\\ -35\\ \\ -0\\		2500		pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, -f=1.0MHz		520		pF	
Reverse Transfer Capacitance	C _{RSS}	1-1:0IVIH2		100		pF	
SWITCHING PARAMETERS							
Total Gate Charge	Q_{G}	\/ -10\/ \/ -50\/		85		nC	
Gate to Source Charge	Q_GS	V _{GS} =10V, V _{DD} =50V, -I _D =1.3A, I _G =100µA		15		nC	
Gate to Drain Charge	Q_GD	IB- 1:3A, IG- 100μA		41		nC	
Turn-ON Delay Time	t _{D(ON)}			35		ns	
Rise Time	t _R	V _{GS} =0~10V, V _{DD} =30V,		320		ns	
Turn-OFF Delay Time	t _{D(OFF)}	I_D =0.5A, R_G =25 Ω		210		ns	
Fall-Time	t _F			200		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current	Is				40	Α	
Maximum Body-Diode Pulsed Current	I _{SM}				160	Α	
Drain-Source Diode Forward Voltage	V_{SD}	I _S =40A, V _{GS} =0V			1.48	V	
Body Diode Reverse Recovery Time	t _{RR}	V_{GS} =0V, I_S =30A		150		ns	
Body Diode Reverse Recovery Charge	Q_{RR}	dI_F/d_t =100A/ μ s		0.9		μC	

■ TYPICAL CHARACTERISTICS



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